

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): An impurity introducing method, including

a first plasma irradiation step of carrying out plasma irradiation for realization of amorphous in which a surface of a semiconductor substrate is changed to an amorphous situation, and a second plasma irradiation step of carrying out plasma doping impurities so as to form a shallow junction in the semiconductor substrate, and

including a resetting step of resetting a plasma irradiation condition, on the occasion of shifting from the first plasma irradiation step to the second plasma irradiation step,

wherein the resetting step includes a step of resetting an initial condition of a ~~plasma generation source~~ ~~platen~~ RF power supply system so as to adapt to plasma which is used in each step.

Claim 2 (canceled)

Claim 3 (previously presented): The impurity introducing method as set forth in Claim 1, wherein the resetting step includes a step of resetting an initial condition of a matching point of a matching circuit so as to adapt to plasma which is used in each step.

Claim 4 (currently amended): The impurity introducing method as set forth in ~~any one of Claims 1 through 3~~ claim 1, wherein the resetting step includes a step of ~~stopping~~ electric discharge once and then, resetting it, on the occasion of shifting from the first plasma irradiation step to the second plasma irradiation step.

Claim 5 (currently amended): The impurity introducing method as set forth in ~~any one of Claims 1 through 3~~ claim 1, wherein the resetting step includes a step of decreasing ~~and changing~~ bias power and thereafter, applying desired bias power, on the occasion of shifting from the first plasma irradiation step to the second plasma irradiation step.

Claim 6 (currently amended): The impurity introducing method as set forth in ~~any one of Claims 1 through 3~~ claim 1, wherein the resetting step includes a step ~~includes one~~ of decreasing pressure and changing other conditions except pressure, and thereafter, setting desired pressure, on the

occasion of shifting from the first plasma irradiation step to the second plasma irradiation step.

Claim 7 (currently amended): The impurity introducing method as set forth in ~~any one of Claims 1 through 6~~ claim 1, characterized in that the second plasma irradiation step is carried out after the first plasma irradiation step.

Claim 8 (original): The impurity introducing method as set forth in Claim 7, wherein it is configured in such a manner that the first plasma irradiation step is carried out after the second plasma irradiation step.

Claim 9 (currently amended): The impurity introducing method as set forth in ~~any one of Claims 1 through 6~~ claim 1, wherein it is configured in such a manner that the first plasma irradiation step is carried out prior to the second plasma irradiation step.

Claim 10 (currently amended): The impurity introducing method as set forth in ~~any one of Claims 1 through 9~~ claim 1, characterized in that gas seed, which is used in the fist plasma irradiation step, includes helium and or neon.

Claim 11 (currently amended) : The impurity introducing method as set forth in ~~any one of Claims 1 through 9~~ claim 1, wherein gas seed, which is used in the second plasma irradiation step, includes at least one of a group comprising Ar, Kr, Xe, and Rn.